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"Enhanced Comparison of Lock-in Thermography and Magnetic Microscopy for 3D Defect Localization of System in Packages""Non Destructive Failure Analysis of 3D Electronic Packages Using Both Electro Optical Terahertz Pulse Reflectometry and 3D X-ray Computed Tomography"; "Failure Analysis Using Scanning Acoustic Microscopy for Diagnostics of Electronic Devices and 3D System Integration Technologies"; "Nanoprobing Applications"; "Analysis of an Anomalous Transistor Exhibiting Dual-Vt Characteristics and Its Cause in a 90 nm Node CMOS Technology"

"Study of Static Noise Margin, Cell Stability and Influence of Electron Beam on Sub-30 nm SRAM Using SEM-Based Nanoprobing with 8 Nanoprobes""Leaky Device Channel Anomaly Identification and Case Study by Nano-Probing Technique, Curve Fitting, and Model Analysis"; "Photon Based Techniques: An Understanding"; "Photon Emission Spectra of FETs as Obtained by InGaAs Detector"; "Near-Infrared Photon Emission Spectroscopy Trends in Scaled SOI Technologies"

"Characterization and TCAD Simulation of 90 nm Technology PMOS Transistor Under Continuous Photoelectric Laser Stimulation for Failure Analysis Improvement"
